



100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)} max	I _D T _A = +25℃
-100V	350mΩ @ V _{GS} = -10V	-2.4A
-100 V	450mΩ @ V _{GS} = -4.5V	-2.1A

Description and Applications

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Motor Control
- DC-DC Converters
- Power Management Functions
- Relay and Solenoid Driving

Features and Benefits

- Fast Switching Speed
- Low Input Capacitance
- Low Gate Drive
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

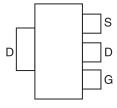
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208
- Weight: 0.112 grams (Approximate)

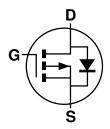
SOT223



Top View



Pin Out - Top



Equivalent Circuit

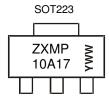
Ordering Information (Note 5)

Product	Case	Packaging
ZXMP10A17GQTA	SOT223	1,000/Tape & Reel
ZXMP10A17GQTC	SOT223	4,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Automotive, AEC-Q101 and standard products are electrically and thermally the same, except where specified. For more information, please refer to http://www.diodes.com/quality/product_grade_definitions/.
- 5. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXMP10A17 = Product Type Marking Code YWW = Date Code Marking Y = Year (ex: 4 = 2014) WW = Week (01 - 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	-100	V	
Gate-Source Voltage		V_{GS}	±20	٧	
		(Note 7)		-2.4	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70 ^{\circ}\text{C} \text{ (Note 7)}$	I _D	-1.9	Α
		(Note 6)		-1.7	
Pulsed Drain Current	V _{GS} = 10V	(Note 8)	I _{DM}	-9.4	Α
Continuous Source Current	(Body Diode)	(Note 7)	I _S	-4.5	Α
Pulsed Source Current (Body Diode) (Note 8)		I _{SM}	-9.4	A	

Thermal Characteristics (@T_A = +25 °C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit	
Power dissipation	(Note 6)	В	2.0 16	W mW/℃	
Linear derating factor	(Note 7)	P _D	3.9 31		
The second Decistors of Location to Applicat	(Note 6)	Б	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 7)	$R_{\theta JA}$	32.0		
Thermal Resistance, Junction to Case	(Note 6)	$R_{ heta JC}$	7.7		
Operating and storage temperature range		T _J , T _{STG}	-55 to 150	.€	

Electrical Characteristics @TA = 25 °C unless otherwise specified

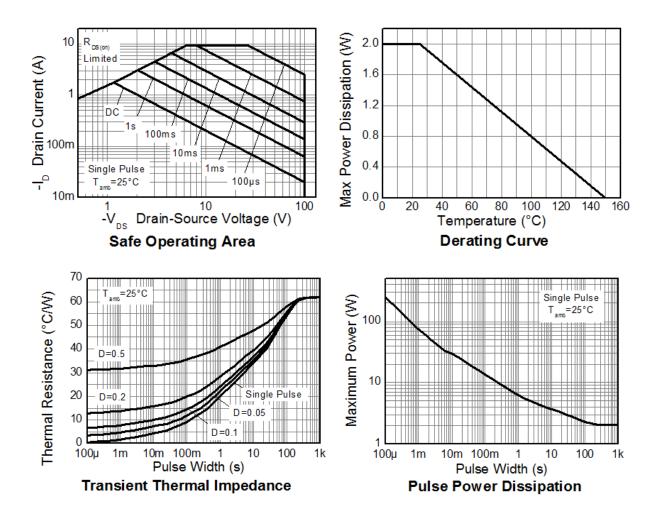
Characteristic	Symbol	Min	Тур	Max	Unit	Test C	ondition
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	—	-0.5	μΑ	V _{DS} = -100V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	V _{GS} = ±20V, V _{DS} = 0V	
ON CHARACTERISTICS			•	•	•		
Gate Threshold Voltage	V _{GS(th)}	-2.0	_	-4.0	V	I_{D} = -250 μ A, V_{DS} = V_{GS}	
Static Drain Source On Desigtance (Note 0)	Б			0.350	Ω	V_{GS} = -10V, I_{D} =	-1.4A
Static Drain-Source On-Resistance (Note 9)	R _{DS} (ON)		_	0.450	12	V _{GS} = -6V, I _D = -1	1.2A
Forward Transconductance (Notes 9 & 10)	g fs	_	2.8	_	S	V _{DS} = -15V, I _D = -1.4A	
Diode Forward Voltage (Note 9)	V _{SD}	_	-0.85	-0.95	V	I _S = -1.7A, V _{GS} = 0V	
Reverse recovery Time (Note 10)	t _{rr}		33	_	ns	I _F = -1.5A, di/dt= 100A/μs	
Reverse recovery Charge (Note 10)	Q _{rr}	_	48	_	nC		
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	C _{iss}	_	424	_	pF	V _{DS} = -50V, V _{GS} = 0V -f= 1MHz	
Output Capacitance	Coss	_	36.6	_	pF		
Reverse Transfer Capacitance	C _{rss}	_	29.8	_	pF		
Total Gate Charge (Note 11)	Qg	_	7.1	_	nC	V _{GS} = -6.0V	
Total Gate Charge (Note 11)	Qg	_	10.7	_	nC	V _{DS} = -50V V _{GS} = -10V I _D = -1.4A	
Gate-Source Charge (Note 11)	Q _{gs}	_	1.7	_	nC		
Gate-Drain Charge (Note 11)	Q _{gd}	_	3.8	_	nC		
Turn-On Delay Time (Note 11)	t _{D(on)}	_	3.0	_	ns		
Turn-On Rise Time (Note 11)	t _r		3.5	_	ns	V_{DD} = -15V, V_{GS} = -10V I_{D} = -1A, $R_{G} \cong 6.0\Omega$	
Turn-Off Delay Time (Note 11)	t _{D(off)}	_	13.4	_	ns		
Turn-Off Fall Time (Note 11)	t _f	_	7.2	_	ns		

Notes:

- 6. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 7. Same as Note 6, except the device is measured at $t \le 10$ seconds.
- 8. Same as Note 6, except the device is pulsed with D=0.02 and pulse width $300 \mu s$. The pulse current is limited by the maximum junction temperature.
- 9. Measured under pulsed conditions. Pulse width \leq 300 μ s; duty cycle \leq 2%.
- 10. For design aid only, not subject to production testing.
 11. Switching characteristics are independent of operating junction temperatures.

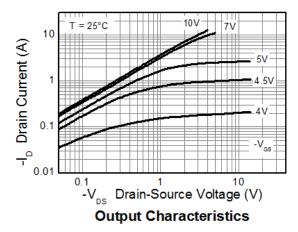


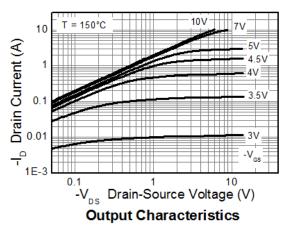
Thermal Characteristics

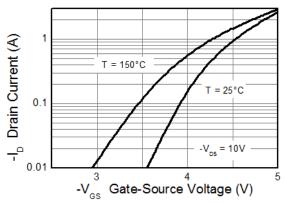


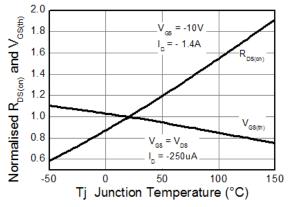


Typical Characteristics



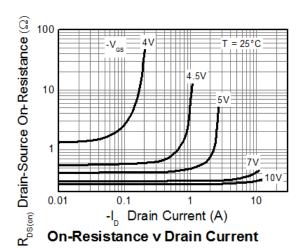


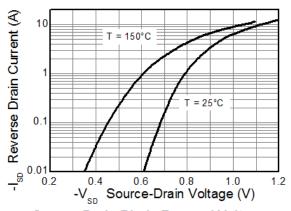




Typical Transfer Characteristics

Normalised Curves v Temperature



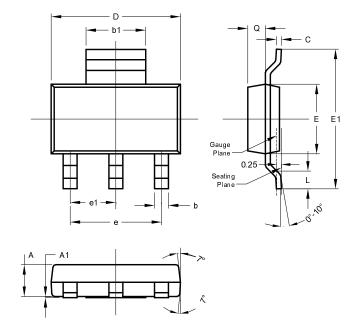


Source-Drain Diode Forward Voltage



Package Outline Dimensions

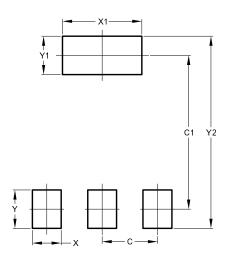
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
Х	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
V2	8 00		



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